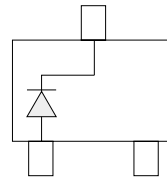


SWITCHING DIODE

FEATURES

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

MARKING : A6



BAS16



MAXIMUM RATINGS (TA=25°C unless otherwise noted)

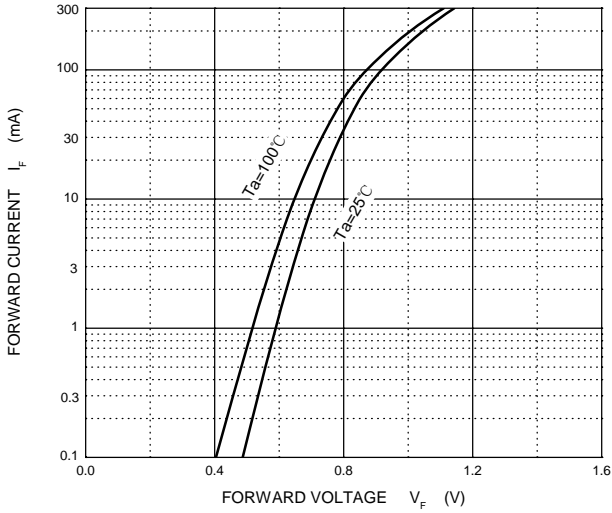
Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	100	V
Peak Repetitive Peak Reverse Voltage	V_{RRM}	75	V
Working Peak Reverse Voltage	V_{RWM}		
DC Blocking Voltage	V_R		
RMS Reverse Voltage	$V_{R(RMS)}$	53	V
Forward Continuous Current	I_{FM}	300	mA
Average Rectified Output Current	I_O	150	mA
Peak Forward Surge Current @t=1.0μs	I_{FSM}	2.0	A
		@t=1.0s	
Power Dissipation	P_D	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_j	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

Electrical Ratings @TA=25°C

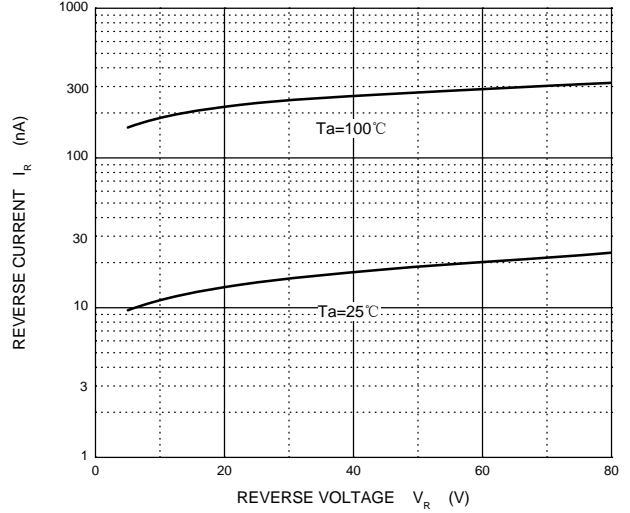
Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	$I_R=100\mu A$	75		V
Reverse voltage leakage current	I_R	$V_R=75V$		1	μA
Forward voltage	V_F	$I_F=1mA$		0.715	V
		$I_F=10mA$		0.855	
		$I_F=50mA$		1	
Diode capacitance	C_D	$V_R=0, f=1MHz$		2	pF
Reveres recovery time	t_{rr}	$I_F=I_R=10mA, I_{rr}=0.1 \times I_R,$ $R_L=100\Omega$		6	ns

BAS16 Typical Characteristics

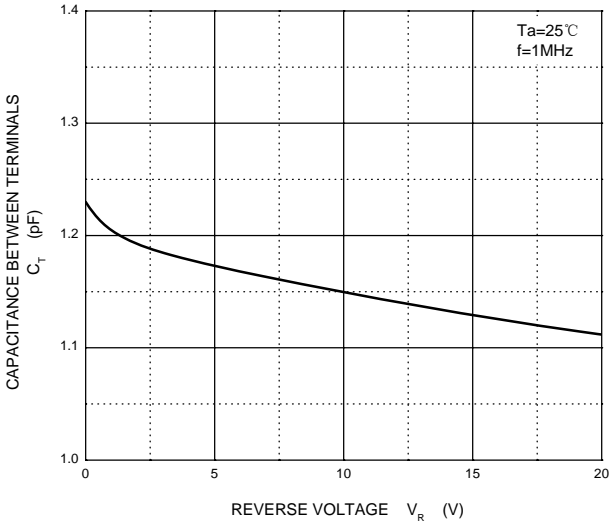
Forward Characteristics



Reverse Characteristics



Capacitance Characteristics



Power Derating Curve

